



PRODUCT/PROCESS CHANGE NOTIFICATION

PCN APG-MID/13/8204
Dated 05 Nov 2013

MANUFACTURING IMPROVEMENTS APPLIED TO PICTUS FAMILY

Table 1. Change Implementation Schedule

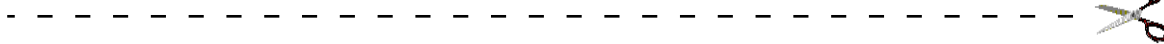
Forecasted implementation date for change	15-May-2014
Forecasted availability date of samples for customer	15-Apr-2014
Forecasted date for STMicroelectronics change Qualification Plan results availability	15-Dec-2013
Estimated date of changed product first shipment	15-Jul-2014

Table 2. Change Identification

Product Identification (Product Family/Commercial Product)	PICTUS FAMILY
Type of change	Waferfab additional location
Reason for change	Corporate Process Roadmap
Description of the change	Qualification of Crolles as additional diffusion plant plus qualification of Malta plant as additional assy plant. See details
Change Product Identification	Dedicated marking traceability on products and labels
Manufacturing Location(s)	

Table 3. List of Attachments

Customer Part numbers list	
Qualification Plan results	



Customer Acknowledgement of Receipt		PCN APG-MID/13/8204	
Please sign and return to STMicroelectronics Sales Office		Dated 05 Nov 2013	
<input type="checkbox"/> Qualification Plan Denied <input type="checkbox"/> Qualification Plan Approved <input type="checkbox"/> Change Denied <input type="checkbox"/> Change Approved	Name:		
	Title:		
	Company:		
	Date:		
	Signature:		
Remark			
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DOCUMENT APPROVAL

Name	Function
Duncan, Martin Russell	Marketing Manager
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Mervic, Alberto	Q.A. Manager

MANUFACTURING IMPROVEMENTS APPLIED TO PICTUS FAMILY

WHAT:

In order to meet the forecasted increase of demand for CMOSM10 products (90 nm), we are going to put in place the following initiatives:

- 1) activate Crolles 12" plant as a second and high volumes manufacturing source beside Rousset R8 8". The above manufacturing plant activation has been already communicated through PCN APG-MID/13/7698 issued in March 2013.
- 2) introduce the CuPd wire bonding as an alternative to Au wire bonding.
- 3) activate Malta plant as a second and high volumes Assembly source beside Muar. The above manufacturing plant activation has been already communicated through PCN APG-MID/13/7972 issued in July 2013.

WHY:

Corporate Process Roadmap

On customer request the above mentioned PCNs has been split by product family keeping unchanged the overall Company strategy.

HOW:

Here attached are the qualification reports for the process test vehicles: FP50 (Pictus 512K) & FA80 (Andorra 4M cut3.0).

We forecast to complete the changes (qualification of the products in Crolles, CuPd wire bonding, Malta assy plant) by end of Q1/2014.

Traceability will be granted by ST system. A dedicated code marked on the parts will enable to distinguish between diffusion sites (see attached document).

See below list of relevant commercial products with the changes to be applied.

WHEN:


Sampling: on customer request starting December 2013

PPAP in April 2014

Production & shipment progressively from Q2 2014

Involved products

	Activation of Crolles as high volume manufacturing source	Introduction of CuPd wire	Introduction of Malta plant as main source for QFP 64/100 pin
SPC56xP60L5x	YES	YES	NO
SPC56xP54L5x	YES	YES	NO
SPC560P50L5x	YES	YES	NO
SPC560P44L5x	YES	YES	NO
SPC56xP60L3x	YES	YES	YES
SPC56xP54L3x	YES	YES	YES
SPC560P50L3x	YES	YES	YES
SPC560P44L3x	YES	YES	YES
SPC560P40L3x	YES	YES	YES
SPC560P34L3x	YES	YES	YES
SPC560P40L1x	YES	YES	YES
SPC560P34L1x	YES	YES	YES

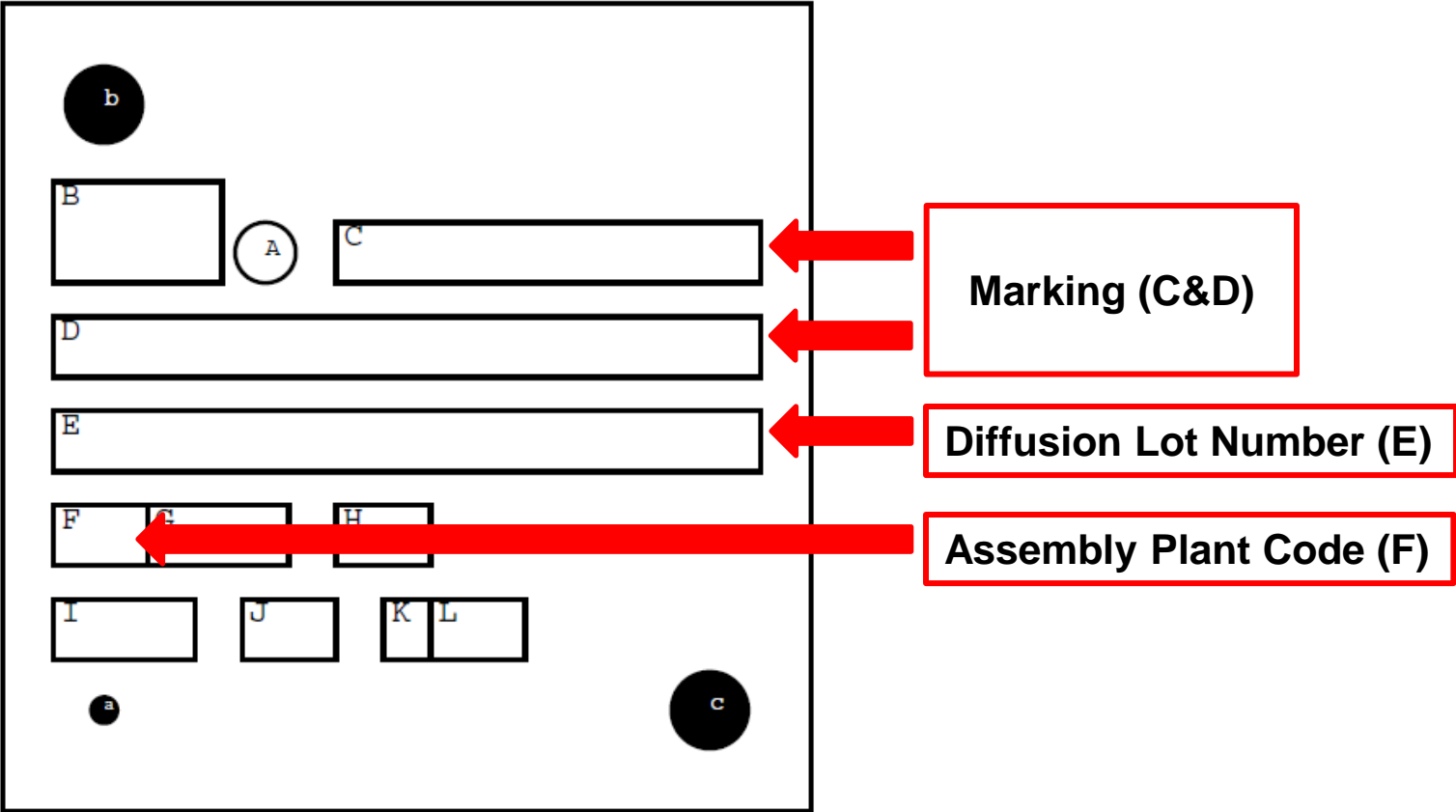


PCN APG-MID/13/8204

Pictus Family Ordering Code and Marking info

APG MRD Microcontroller

PACKAGE FACE : TOP



	Pictus 1M Cut1.1 (Rousset Au Muar)	Pictus 1M Cut1.1 (Crolles CuPd Malta)
Ordering code	SPC56AP54L3BEFBR	
Finish Good code	6AP54L3B2EFBR700	6AP54L3B E EFBR700
Silicon code	FP60ABG	FP60AB Q
Diff Lot Number (E)	VG-----	V Q -----
Marking (C)	AB	AB
Marking (D)	SPC56AP54L3	SPC56AP54L3
Marking (F)	99	22

LQFP100

	Pictus 1M Cut1.1 (Rousset Au Malta)	Pictus 1M Cut1.1 (Crolles CuPd Malta)
Ordering code	SPC560P60L5CEFAY	
Finish Good code	60P60L5C2EFAY700	60P60L5C E EFAY700
Silicon code	FP60ABG	FP60AB Q
Diff Lot Number (E)	VG-----	V Q -----
Marking (C)	AB	AB
Marking (D)	SPC560P60L5	SPC560P60L5
Marking (F)	22	22

LQFP144

Red digit: differentiation for new silicon cut

	Pictus 512K Cut3.5 (Rousset Au Muar)	Pictus 512k Cut3.5 (Rousset Au Malta)	Pictus 512k Cut3.5 (Crolles CuPd Malta)
Ordering code	SPC560P44L3CEFAY		
Finish Good code	60P44L3CBEFAY200	60P44L3CMEFAY200	60P44L3CEEFAY200
Diff Lot Number (E)	VG-----	VG-----	VQ-----
Silicon code	FP50BE2	FP50BE2	FP50BEQ
Marking (C)	BE	BE	BE
Marking (D)	SPC560P44	SPC560P44	SPC560P44
Marking (F)	99	22	22

LQFP100

	Pictus 512K Cut3.5 (Rousset Au Malta)		Pictus 512k Cut3.5 (Crolles CuPd Malta)
Ordering code	SPC560P50L5BEABY		
Finish Good code	60P50L5BBEABY200		60P50L5BEEABY200
Diff Lot Number (E)	VG-----		VQ-----
Silicon code	FP50BE2		FP50BEQ
Marking (C)	BE		BE
Marking (D)	SPC560P50		SPC560P50
Marking (F)	22		22

LQFP144

Pictus 256K

5

	Pictus 256K Cut1.2 (Rousset Au Muar)	Pictus 256k Cut1.2 (Rousset Au Malta)	Pictus 256k Cut1.2 (Crolles CuPd Malta)
Ordering code	SPC560P40L3BEAAR		
Finish Good code	60P40L3B3EAAR400	60P40L3B M EAAR400	60P40L3B E AAR400
Diff Lot Number (E)	VG-----	VG-----	V Q -----
Silicon code	FP40AC2	FP40AC2	FP40AC Q
Marking (C)	AC	AC	AC
Marking (D)	SPC560P40	SPC560P40	SPC560P40
Marking (F)	99	22	22

LQFP100

	Pictus 256K Cut1.2 (Rousset Au Muar)	Pictus 256k Cut1.2 (Rousset Au Malta)	Pictus 256k Cut1.2 (Crolles CuPd Malta)
Ordering code	SPC560P40L1BEAAR		
Finish Good code	60P40L1B3EAAR400	60P40L1B M EAAR400	60P40L1B E AAR400
Diff Lot Number (E)	VG-----	VG-----	V Q -----
Silicon code	FP40AC2	FP40AC2	FP40AC Q
Marking (C)	AC	AC	AC
Marking (D)	SPC560P40	SPC560P40	SPC560P40
Marking (F)	99	22	22

LQFP64



Reliability Report
Andorra 4M
FAB transfer

General Information	
Product Line	FA80
Product Description	Andorra 4M cut 3.0
Commercial Product	SPC564A80
Product Group	APG
Product division	MID
Silicon process technology	CMOS M10

Locations	
Wafer fab location	Crolles 2
Final Assessment	
Reliability assessment	Qualification Passed as per Q100 rev G grade 1

DOCUMENT HISTORY

Version	Date	Author	Comment
1.0	30/04/2013	M. De Tomasi	First Document release

RELEASED DOCUMENT



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1 RELIABILITY EVALUATION OVERVIEW

1.1 Objectives

Aim of this document is to report the reliability trials results of Andorra 4M Cut 3.0 qualification.

Andorra 4M cut 3.0 is processed in Crolles FAB using CMOS M10 (90 nm) technology and it is assembled in Malta-ST assy line for LQFP176 package with gold wire.

The M10 (90nm technology) process was qualified in Rousset R8 Fab in wk922 using three logic test chips and a Flash test chip as test vehicles. Andorra 4M cut 2.0 was qualified in Rousset in Q1 2011.

Considering that Andorra4M is the first M10 product with 6 metal layers and FLS Flash diffused in Crolles, no similarity with other qualified products could be considered.

The qualification exercise will be based on 3 diffusion lots coming from Crolles: assy reports required on all qualification lots.

The qualification exercise is in respect of Q100 rev G specification.

1.2 Conclusions

All qualification trials have been completed with positive results. Neither functional nor parametric rejects were detected at final electrical testing.

Parameter drift analysis performed on samples submitted to die oriented test showed a good stability of the main electrical monitored parameters.

Package oriented tests have not put in evidence any criticality.

On the ground of the overall positive results we can conclude that Andorra 4M cut 3.0 in LQFP176 can be qualified in accordance to AEC-Q100 Grade1 RevG.

2 TRACEABILITY

2.1 Wafer fab information

DIE FEATURES	
Diffusion Site	<i>Crolles 2</i>
Wafer Diameter (inches)	12
Process Technology	<i>CMOS M10</i>
Passivation	PSG - Nit UV
Die finishing back side	Lapped Silicon

2.2 Package outline/Mechanical data

LQFP 176	
Package Description	<i>LQFP 176 24x24x1.4</i>
Assembly Site	<i>ST KIRKOP – MALTA</i>
Die Attach material	ABLEBOND 3280T
Molding compound	SUMITOMO EME-G700LS
Substrate/Leadframe	LQFP 176L 24SQ RgAg
Wires bonding materials/diameters	WIRE Au 2N GPG2 D0.9

2.3 Final testing information:

PACKAGE FEATURES	
Electrical Testing manufacturing location	: <i>ST KIRKOP – MALTA</i>
Tester	: Teradyne J750

3 RELIABILITY PLAN AND TESTS RESULTS

3.1 Conditions

Room test temperature is 25°C
 Hot test temperature is 150°C
 Cold test temperature is -40°C

3.2 Tables entry legend

Symbol	How to read
<input type="checkbox"/>	Action or condition has not to be considered
<input checked="" type="checkbox"/>	The action/condition has been done/applied during the trial
N.P.	The trial or readout is not in the Qualification Plan and thus has not been performed

3.3 Accelerated Environmental Stress Test (Q100 Group A)

N	Test		Step	RESULTS			Notes
	TEST NAME	CONDITIONS [SPEC]		LOT 1	LOT 2	LOT 3	
1	Pre Conditioning MSL 3	[J-STD-020] <input checked="" type="checkbox"/> Testing at Room <input checked="" type="checkbox"/> Testing at Hot <input type="checkbox"/> Testing at Cold <input checked="" type="checkbox"/> Sonoscan pre / post <input checked="" type="checkbox"/> 100 Temperature Cycles 24h bake@125°C, 192h@30°C/60%RH 3x Reflow simulation 260°C Peak Temp	Pre	0/231	0/231	0/231	
			Post	0/231	0/231	0/231	
2	THB Temperature Humidity Bias	[JESD22-A101/A110] <input checked="" type="checkbox"/> AfterJedec PC MSL3 <input checked="" type="checkbox"/> Testing at Room <input checked="" type="checkbox"/> Testing at Hot <input type="checkbox"/> Testing at Cold Ta=85°C, 85%RH, 1000hrs	500 hrs	0/77	0/77	0/77	
			1000 hrs	0/77	0/77	0/77	
3	AC Autoclave	[JESD22-A102/A118] <input checked="" type="checkbox"/> AfterJedec PC MSL3 <input checked="" type="checkbox"/> Testing at Room <input type="checkbox"/> Testing at Hot <input type="checkbox"/> Testing at Cold P=2.08atm Ta=121°C, 96hrs	96 hrs	0/77	0/77	0/77	
4	TC Temperature Cycling	[JESD22-A104] <input checked="" type="checkbox"/> AfterJedec PC MSL3 <input checked="" type="checkbox"/> Testing at Room <input checked="" type="checkbox"/> Testing at Hot <input checked="" type="checkbox"/> Testing at Cold <input checked="" type="checkbox"/> Sonoscan pre / post <input checked="" type="checkbox"/> WPT pre / post <input checked="" type="checkbox"/> WBS pre / post Ta=-50°C /+150 °C 1000 cyc	500 cyc	0/77	0/77	0/77	
			1000 cyc	0/77	0/77	0/77	



5	PTC Power Temperature Cycle	[JESD22-A105] <input type="checkbox"/> After Jedec PC MSL3 <input type="checkbox"/> Testing at Room <input type="checkbox"/> Testing at Hot <input type="checkbox"/> Testing at Cold Ta=-40°C /+125 °C 1000 cyc	1000 cyc	N.P.	N.P.	N.P.	Not required on Andorra 4M
6	HTSL High Temperature Storage Lifetime	[JESD22-A103] Ta= 150°C 1000hrs (2000hrs <i>monitoring</i>)	1000 hrs	N.P.	N.P.	N.P.	See HTDR trial

3.4 Accelerated Lifetime Simulation Test (Q100 Group B)

N	TEST NAME	Test	Step	Results			Notes
		CONDITIONS [SPEC]		Lot 1	Lot 2	Lot 3	
1	HTOL High Temp. Operating Life	[JESD22-A108] <input checked="" type="checkbox"/> After Jedec PC MSL3 <input checked="" type="checkbox"/> After 1k W/E cyc @125°C <input checked="" type="checkbox"/> Testing at Room, Hot, Cold <input checked="" type="checkbox"/> Drift Analysis on Key parameters at Room, Hot, Cold Ta=125°C, Tj=150°C VDD+20% 1000hrs	168 hrs	0/77	0/77	0/77	
			500 hrs	0/77	0/77	0/77	
			1000 hrs	0/77	0/77	0/77	
2	ELFR Early Life Failure Rate	[AEC Q100-008] <input checked="" type="checkbox"/> Testing at Room, Hot, Cold Ta= 125°C, Tj=150°C, 24+24hrs	24hrs	0/77	0/77	0/77	
			48hrs	0/77	0/77	0/77	
3	HTDR High Temp. Data Retention	[AEC Q100-005] <input checked="" type="checkbox"/> After Jedec PC MSL3 <input checked="" type="checkbox"/> Testing at Room <input checked="" type="checkbox"/> Testing at Hot <input type="checkbox"/> Testing at Cold <input checked="" type="checkbox"/> After 1k W/E cyc @125°C <input checked="" type="checkbox"/> Vth Drift Analysis Ta= 150°C, All0 Pattern 2000hrs	168 hrs	0/77	0/77	0/77	
			500 hrs	0/77	0/77	0/77	
			1000 hrs	0/77	0/77	0/77	
			2000 hrs	0/77	0/77	0/77	
4.a	FET @25°C	[AEC Q100-005] <input checked="" type="checkbox"/> Drift Analysis on Flash key parameters at Room, Hot, Cold Ta= 25°C 100k Write/Erase cyc	10k cyc	0/77	N.P.	N.P.	
			50k cyc	0/77	N.P.	N.P.	
			100k cyc	0/77	N.P.	N.P.	
4.b	HTDR After FET	<input checked="" type="checkbox"/> Vth Drift Analysis Ta= 150°C, All0 Pattern 168hrs	168 hrs	0/77	N.P.	N.P.	
5.a	FET @125°C	[AEC Q100-005] <input checked="" type="checkbox"/> Drift Analysis on Flash key parameters at Room, Hot, Cold Ta= 125°C 100k Write/Erase cyc	10k cyc	0/77	0/77	0/77	
			50k cyc	0/77	0/77	0/77	
			100k cyc	0/77	0/77	0/77	
5.b	HTDR After FET	<input checked="" type="checkbox"/> Vth Drift Analysis Ta= 150°C, All0 Pattern 168hrs	168 hrs	0/77	0/77	0/77	

6.a	FET @-40°C	[AEC Q100-005]	10k cyc	N.P.	0/77	N.P.	
		<input checked="" type="checkbox"/> Drift Analysis on Flash key parameters at Room, Hot, Cold	50k cyc	N.P.	0/77	N.P.	
		Ta= -40°C 100k Write/Erase cyc	100k cyc	N.P.	0/77	N.P.	
6.b	HTDR After FET	<input checked="" type="checkbox"/> Vth Drift Analysis Ta= 150°C, All0 Pattern 168hrs	168 hrs	N.P.	0/77	N.P.	
7	LTDR Low Temp. Data Retention	[AEC Q100-005]	500 hrs	0/77	N.P.	N.P.	
		<input checked="" type="checkbox"/> Vth Drift Analysis After 1k W/E cyc @25°C Ta= 60°C, All0 Pattern 2000hrs	1000 hrs	0/77	N.P.	N.P.	
			2000 hrs	0/77	N.P.	N.P.	
8	LTDR Low Temp. Data Retention	[AEC Q100-005]	500 hrs	0/77	N.P.	N.P.	
		<input checked="" type="checkbox"/> Vth Drift Analysis After 10k W/E cyc @25°C Ta= 60°C, All0 Pattern 2000hrs	1000 hrs	0/77	N.P.	N.P.	
			2000 hrs	0/77	N.P.	N.P.	
9	LTDR Low Temp. Data Retention	[AEC Q100-005]	500 hrs	0/77	N.P.	N.P.	
		<input checked="" type="checkbox"/> Vth Drift Analysis After 100k W/E cyc @25°C Ta= 60°C, All0 Pattern 2000hrs	1000 hrs	0/77	N.P.	N.P.	
			2000 hrs	0/77	N.P.	N.P.	
10	Flip Bit	[AEC Q100-005]	168 hrs	N.P.	0/77	N.P.	
		<input checked="" type="checkbox"/> Vth Drift Analysis After 1 W/E cyc @25°C	500 hrs	N.P.	0/77	N.P.	
		Ta= 25°C, Chk Pattern 1000hrs	1000 hrs	N.P.	0/77	N.P.	
11	Read Disturb	After 10 W/E cyc @25°C Ta= 25°C; 4,5V Stress <1ppm after 6000hrs with ECC	Final	N.P.	0/77	N.P.	
12	Read Disturb	After 10k W/E cyc @25°C Ta= 25°C; 4,5V Stress <1ppm after 1 sec with ECC	Final	N.P.	N.P.	0/77	

3.5 Package Assembly Integrity Test (Q100 Group C)

N	TEST NAME	Test	Step	Results			Notes
		CONDITIONS [SPEC]		LQFP176	LQFP144	LQFP100	
1	WBS Wire Bond Shear	[AEC Q100-001] At appropriate time interval for each bonder to be used 30 bonds x 5 devices	Final result	Done	Done	Done	Assy report
2	WBP Wire Bond Pull	[MIL-STD883 method 2011] 30 bonds x 5 devices	Final result	Done	Done	Done	Assy report
3	SD Solderability	[JEDEC JEDES22-B102] > 95% lead coverage	Final result	Done	Done	Done	Assy report
4	PD Physical Dimension	[JEDEC JEDES22-B100 and B108]	Final result	Done	Done	Done	Assy report
5	SBS Solder Ball Shear	[AEC Q100-010]	Final result	N.A.	N.A.	N.A.	Not applicable
6	LI Lead Integrity	[JEDEC JEDES22-B105]	Final result	N.A.	N.A.	N.A.	Not applicable

3.6 Die Fabrication Reliability Test (Q100 Group D)

N	TEST NAME	Test	Step	RESULTS	Notes
		CONDITIONS			
1	EM Electromigration	The data, test method, calculation and internal criteria should be available to the customer upon request for new technologies	Final result	DONE	Process qualification
2	TDDB Time Dependent Dielectric Breakdown	The data, test method, calculation and internal criteria should be available to the customer upon request for new technologies	Final result	DONE	Process qualification
3	HCI Hot Carrier Injection	The data, test method, calculation and internal criteria should be available to the customer upon request for new technologies	Final result	DONE	Process qualification
4	NBTI Negative Bias Temperature Instability	The data, test method, calculation and internal criteria should be available to the customer upon request for new technologies	Final result	DONE	Process qualification
5	SM Stress Migration	The data, test method, calculation and internal criteria should be available to the customer upon request for new technologies	Final result	DONE	Process qualification



3.7 Electrical Verification Test (Q100 Group E)

Test			Step	RESULTS	Notes
N	TEST NAME	CONDITIONS [AEC Q100]			
1.a	ESD HBM	HBM = 2kV	Final result	PASSED	
1.b	ESD MM	MM = 200V	Final result	PASSED	
1.c	ESD CDM	CDM = 500V / 750V corner only	Final result	PASSED	
2.a	LU	Class II - Level A (+/- 100mA)	Final result	PASSED	
2.b	LU	Class II - Level A (1,5 x Vmax)	Final result	PASSED	
3	ED Electrical Distribution	[AEC Q100-009] <input checked="" type="checkbox"/> Testing at Room <input checked="" type="checkbox"/> Testing at Hot <input checked="" type="checkbox"/> Testing at Cold	Final result	DONE	
4	FG Fault Grading	[AEC Q100-007] FG shall be = or > 90% for qual units	Final result	DONE by Similarity	Andorra 4M cut 2.0
5	CHAR Characterization	[AEC Q103] Performed on new technologies and part families. <input type="checkbox"/> Testing at Room <input type="checkbox"/> Testing at Hot <input type="checkbox"/> Testing at Cold	Final result	N.P.	Not required by Q100
6	GL Electrothermally- Induced Gate Leakage	[AEC Q100-006] Test before and after GL at room temperature within 96hours of GL stress completion	Final result	DONE	
7	EMC Electromagnetic Compatibility	[SAE J1752/3 – radiated Emission]	Final result	N.P.	Not required by Q100
8	SC Short Circuit Characterization	[AEC Q100-012] Applicable to all smart power devices. This test and statistical evaluation shall be performed per agreement between user and supplier on a case-by-case basis.	Final result	N.A.	Not applicable to Microcontroller
9	SER Soft Error Rate	[JEDEC Un-accelerated: JESD89-1 or Accelerated: JESD89-2 & JESD89-3] Applicable to devices with memory sizes 1Mbit SRAM or DRAM based cells. Either test option (un-accelerated or accelerated) can be performed, in accordance to the referenced specifications. This test and its accept criteria is performed	Final result	DONE	



3.8 Defect Screening Test (Q100 Group F)

Test			Step	RESULTS	Notes
N	TEST NAME	CONDITIONS			
1	PAT Process Average testing	[AEC Q101]	Final result	IMPLEMENTED	
2	SBA Statistical Bin/Yield Analysis	[AEC Q102]	Final result	IMPLEMENTED	

Reliability Report
Pictus 512K
Fab Transfer

General Information	
Product Line	FP50xx
Product Description	Pictus 512k cut 3.5
Commercial Product	SPC560P50xx, SPC560P44xx
Product Group	APG
Product division	MID
Silicon process technology	CMOS M10

Locations	
Wafer fab location	Crolles 2
Final Assessment	
Reliability assessment	Qualification Passed as per Q100 rev G grade 1

DOCUMENT HISTORY

Version	Date	Author	Comment
0.1	29/01/2013	L. Cola	First document draft
0.5	07/02/2013	L. Cola	First document release with preliminary results available
0.6	22/02/2013	L. Cola	Document Format review
1.0	26/06/2013	R. Enrici Vaion	Cut3.5 qualification strategy
1.1	1/07/2013	R. Enrici Vaion	General Information updated

RELEASED DOCUMENT



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1 RELIABILITY EVALUATION OVERVIEW

1.1 Objectives

Aim of this document is to report the reliability trials results achieved on Pictus 512k Cut 3.4 and Cut 3.5 qualification exercise, in order to release the device to production volume in Crolles.

Pictus 512k is processed in Crolles2 FAB using CMOS M10 (90 nm) technology and it is assembled in Malta-ST assy in LQFP144 package.

Pictus 512k embeds the ST Flash module.

Considering that Pictus 512K is the first M10 product with 4 metal layers and ST Flash diffused in Crolles, no similarity with other products could be considered.

The qualification exercise is based on three diffusion lots of Cut 3.4 coming from Crolles2.

Pictus512k Cut3.5, diffused in Crolles, is qualified by similarity taking into account results achieved with Rousset silicon Pictus 512K cut 3.5 (RR003612AG6050), being a pure design fix independent on process transfer.

Package qualification has been run on one assembly lot using similarity with qualification done on Rousset silicon on Pictus 512K and Bolero512K products, considering that from Back End point of view the differences between Rousset and Crolles Fab have to be considered minor.

The qualification exercise for this new product is in respect of Q100 revG.

1.2 Conclusions

Qualification trials have been completed with positive results on Cut3.4. Neither functional nor parametric rejects were detected at final electrical testing.

Parameter drift analysis performed on samples submitted to die oriented test showed a good stability of the main electrical monitored parameters.

Package trials with Au-wire concluded with positive results.

Pictus 512k Cut3.5 is qualified by similarity without any additional trial required.

2 TRACEABILITY

2.1 Wafer fab information

DIE FEATURES	
Diffusion Site	<i>Crolles 2</i>
Wafer Diameter (inches)	12
Process Technology	<i>CMOS M10</i>
Passivation	PSG - Nit UV
Die finishing back side	Lapped Silicon

2.2 Package outline/Mechanical data

LQFP 144	
Package Description	<i>LQFP 144 20x20x1.4</i>
Assembly Site	<i>ST KIRKOP – MALTA</i>
Die Attach material	GLUE ABLEBOND 3280T
Molding compound	SUMITOMO EME-G700LS
Substrate/Leadframe	LQFP 144L RgAg
Wires bonding materials/diameters	WIRE Au 2N GPG2 D0.9

2.3 Final testing information:

PACKAGE FEATURES	
Electrical Testing manufacturing location	: <i>ST KIRKOP – MALTA</i>
Tester	: Teradyne J750

3 RELIABILITY PLAN AND TESTS RESULTS

3.1 Conditions

Room test temperature is 25°C
 Hot test temperature is 125°C
 Cold test temperature is -40°C

3.2 Tables entry legend

Symbol	How to read
<input type="checkbox"/>	Action or condition has not to be considered
<input checked="" type="checkbox"/>	The action/condition has been done/applied during the trial
N.P.	The trial or readout is not in the Qualification Plan and thus has not been performed

3.3 Environmental stress test (Q100 group A)

N	TEST NAME	Test	Step	Notes	
		CONDITIONS [SPEC]		LQFP144	
1	PC Pre- Conditioning MSL 3	[J-STD-020] <input checked="" type="checkbox"/> Testing at Room <input checked="" type="checkbox"/> Testing at Hot <input type="checkbox"/> Testing at Cold <input checked="" type="checkbox"/> Sonoscan pre / post <input type="checkbox"/> 100 Temperature Cycles 24h bake@ 125°C, 192h@ 30°C/60%RH 3x Reflow simulation 260°C Peak Temp	Pre	0/77 x3 x1 Pictus 512K Crolles 0/77 x 3 x 1 Pictus 512K Rousset 0/77 x 3 x 2 Bolero 512K Rousset	Similarity with Pictus 512K and Bolero 512K diffused in Rousset and assembled in Malta
			Post	0/77 x3 x1 Pictus 512K Crolles 0/77 x 3 x 1 Pictus 512K Rousset 0/77 x 3 x 2 Bolero 512K Rousset	
2	THB Temperature Humidity Bias	[JESD22-A101/A110] <input checked="" type="checkbox"/> AfterJedec PC MSL3 <input checked="" type="checkbox"/> Testing at Room <input checked="" type="checkbox"/> Testing at Hot <input type="checkbox"/> Testing at Cold Ta=85°C, 85%RH, 1000hrs	500 hrs	0/77 Pictus 512K Crolles 0/77 Pictus 512K Rousset 0/77 x 2 Bolero 512K Rousset	Similarity with Pictus 512K and Bolero 512K diffused in Rousset and assembled in Malta
			1000 hrs	0/77 Pictus 512K Crolles 0/77 Pictus 512K Rousset 0/77 x 2 Bolero 512K Rousset	



3	AC Autoclave	<p>[JESD22-A102/A118]</p> <p><input checked="" type="checkbox"/> AfterJedec PC MSL3 <input checked="" type="checkbox"/> Testing at Room <input type="checkbox"/> Testing at Hot <input type="checkbox"/> Testing at Cold <input type="checkbox"/> Die visual inspection post trial</p> <p>P=2.08atm Ta=121°C, 96hrs</p>	96 hrs	<p>0/77 Pictus 512K Crolles</p> <p>0/77 Pictus 512K Rousset</p> <p>0/77 x 2 Bolero 512K Rousset</p>	Similarity with Pictus 512K and Bolero 512K diffused in Rousset and assembled in Malta
4	TC Temperature Cycling	<p>[JESD22-A104]</p> <p><input checked="" type="checkbox"/> AfterJedec PC MSL3 <input checked="" type="checkbox"/> Testing at Room <input checked="" type="checkbox"/> Testing at Hot <input type="checkbox"/> Testing at Cold <input checked="" type="checkbox"/> Sonoscan pre / post <input checked="" type="checkbox"/> WPT pre / post <input checked="" type="checkbox"/> WBS pre / post</p> <p>*Ta=-65°C /+150 °C 500 cyc</p> <p>Ta=-50°C /+150 °C 1000 cyc</p>	500 cyc	<p>*0/77 Pictus 512K Crolles</p> <p>0/77 Pictus 512K Rousset</p> <p>0/77 x 2 Bolero 512K Rousset</p>	Similarity with Pictus 512K and Bolero 512K diffused in Rousset and assembled in Malta
			1000 cyc	<p>0/77 Pictus 512K Rousset</p> <p>0/77 x 2 Bolero 512K Rousset</p>	
5	PTC Power Temperature Cycling	<p>[JESD22-A105]</p> <p><input type="checkbox"/> AfterJedec PC MSL3 <input type="checkbox"/> Testing at Room <input type="checkbox"/> Testing at Hot <input type="checkbox"/> Testing at Cold</p> <p>Ta=-40°C /+125 °C 1000 cyc</p>	1000 cyc	N.P.	Not required on Pictus512K
6	HTSL High Temperature Storage Lifetime	<p>[JESD22-A103]</p> <p><input type="checkbox"/> AfterJedec PC MSL3 <input type="checkbox"/> After 100 TC <input checked="" type="checkbox"/> Testing at Room <input checked="" type="checkbox"/> Testing at Hot <input type="checkbox"/> Testing at Cold <input type="checkbox"/> Sonoscan pre / post <input checked="" type="checkbox"/> WPT pre / post <input checked="" type="checkbox"/> WBS pre / post <input type="checkbox"/> Die visual inspection post trial <input type="checkbox"/> Die cross section post trial</p> <p>*Ta= 175°C 336hrs (500hrs monitor)</p> <p>Ta= 150°C 1000hrs</p>	336 hrs	*0/77 Pictus 512K Crolles	Similarity with Pictus 512K and Bolero 512K diffused in Rousset and assembled in Malta
			500hrs	<p>*0/77 Pictus 512K Crolles</p> <p>0/77 Pictus 512K Rousset</p> <p>0/77 x 2 Bolero 512K Rousset</p>	
			1000hrs	<p>0/77 Pictus 512K Rousset</p> <p>0/77 x 2 Bolero 512K Rousset</p>	

3.4 Lifetime stress test (Q100 Group B)

N	TEST NAME	Test CONDITIONS [SPEC]	Step	Results			Notes
				Lot 1	Lot 2	Lot 3	
1	HTOL High Temp. Operating Life	[JESD22-A108] <input checked="" type="checkbox"/> After Jedec PC MSL3 <input type="checkbox"/> After 100 TC <input checked="" type="checkbox"/> After 1k W/E cyc @125°C <input checked="" type="checkbox"/> Testing at Room, Hot, Cold <input checked="" type="checkbox"/> Drift Analysis on Key parameters at Room, Hot, Cold Ta=125°C, Tj=150°C VDD+20% 1000hrs	0 hrs	0/77	0/77	0/77	
		168 hrs	0/77	0/77	0/77		
		500 hrs	0/77	0/77	0/77		
		1000 hrs	0/77	0/77	0/77		
2	ELFR Early Life Failure Rate	[AEC Q100-008] <input checked="" type="checkbox"/> Testing at Room, Hot, Cold Ta= 125°C, Tj=150°C, 48 hrs	48hrs	0/800	0/800	0/800	
3	HTDR High Temp. Data Retention	[AEC Q100-005] <input checked="" type="checkbox"/> After Jedec PC MSL3 <input checked="" type="checkbox"/> After 1k W/E cyc @125°C <input checked="" type="checkbox"/> Vth Drift Analysis Ta= 150°C, All0 Pattern 1000hrs (2000hrs monitoring)	0 hrs	0/77	0/77	0/77	
		168 hrs	0/77	0/77	0/77		
		500 hrs	0/77	0/77	0/77		
		1000 hrs	0/77	0/77	0/77		
4.a	FET @25°C	[AEC Q100-005] <input checked="" type="checkbox"/> Drift Analysis on Flash key parameters at Room, Hot, Cold Ta= 25°C 100k Write/Erase cyc	10k cyc	0/77	0/77	0/77	
		50k cyc	0/77	0/77	0/77		
		100k cyc	0/77	0/77	0/77		
4.b	HTDR After FET	<input checked="" type="checkbox"/> Vth Drift Analysis Ta= 150°C, All0 Pattern 168hrs	168 hrs	0/77	0/77	0/77	

N	TEST NAME	Test CONDITIONS [SPEC]	Step	Results			Notes
				Lot 1	Lot 2	Lot 3	
5.a	FET @125°C	[AEC Q100-005] <input checked="" type="checkbox"/> Drift Analysis on Flash key parameters at Room, Hot, Cold Ta= 125°C 100k Write/Erase cyc	10k cyc	0/77	N.P.	N.P.	
			50k cyc	0/77	N.P.	N.P.	
			100k cyc	0/77	N.P.	N.P.	
5.b	HTDR After FET	<input checked="" type="checkbox"/> Vth Drift Analysis Ta= 150°C, All0 Pattern 168hrs	168 hrs	0/77	N.P.	N.P.	
6.a	FET @-40°C	[AEC Q100-005] <input checked="" type="checkbox"/> Drift Analysis on Flash key parameters at Room, Hot, Cold Ta= -40°C 100k Write/Erase cyc	10k cyc	0/77	N.P.	N.P.	
			50k cyc	0/77	N.P.	N.P.	
			100k cyc	0/77	N.P.	N.P.	
6.b	HTDR After FET	<input checked="" type="checkbox"/> Vth Drift Analysis Ta= 150°C, All0 Pattern 168hrs	168 hrs	0/77	N.P.	N.P.	
7	LTDR Low Temp. Data Retention	[AEC Q100-005] After 1k W/E cyc @25°C Ta= 60°C, All0 Pattern 1000hrs (2000hrs monitoring)	0 hrs	0/77	N.P.	N.P.	
			500 hrs	0/77	N.P.	N.P.	
			1000 hrs	0/77	N.P.	N.P.	
			2000 hrs	0/77	N.P.	N.P.	
8	LTDR Low Temp. Data Retention	[AEC Q100-005] After 10k W/E cyc @25°C Ta= 60°C, All0 Pattern 1000hrs (2000hrs monitoring)	0 hrs	0/77	N.P.	N.P.	
			500 hrs	0/77	N.P.	N.P.	
			1000 hrs	0/77	N.P.	N.P.	
			2000 hrs	0/77	N.P.	N.P.	
9	LTDR Low Temp. Data Retention	[AEC Q100-005] After 100k W/E cyc @25°C Ta= 60°C, All0 Pattern 1000hrs (2000hrs monitoring)	0 hrs	0/77	N.P.	N.P.	
			500 hrs	0/77	N.P.	N.P.	
			1000 hrs	0/77	N.P.	N.P.	
			2000 hrs	0/77	N.P.	N.P.	
10	Flip Bit	[AEC Q100-005] After 1 W/E cyc @25°C Ta= 25°C, Chk Pattern 1000hrs	0 hrs	0/77	N.P.	N.P.	
			168 hrs	0/77	N.P.	N.P.	
			500 hrs	0/77	N.P.	N.P.	
			1000 hrs	0/77	N.P.	N.P.	

N	TEST NAME	Test	Step	Results			Notes
		CONDITIONS [SPEC]		Lot 1	Lot 2	Lot 3	
11.a	Read Disturb	After 10 W/E cyc @125°C Ta= 25°C; 4,5V Stress 220hrs	Final	0/77	N.P.	N.P.	
11.b	Read Disturb	After 10k W/E cyc @125°C Ta= 25°C; 4,5V Stress 1s	Final	0/77	N.P.	N.P.	

3.5 Package Assembly Integrity Test (Q100 Group C)

N	TEST NAME	Test	Step	Results	Notes
		CONDITIONS [SPEC]			
1	WBS Wire Bond Shear	[AEC Q100-001] At appropriate time interval for each bonder to be used 30 bonds x 5 devices	Final result	Done	Assy report
2	WBP Wire Bond Pull	[MIL-STD883 method 2011] 30 bonds x 5 devices	Final result	Done	Assy report
3	SD Solderability	[JEDEC JEDES22-B102] > 95% lead coverage	Final result	Done	Assy report
4	PD Physical Dimension	[JEDEC JEDES22-B100 and B108]	Final result	Done	Assy report
5	SBS Solder Ball Shear	[AEC Q100-010]	Final result	N.A.	Not applicable
6	LI Lead Integrity	[JEDEC JEDES22-B105]	Final result	N.A.	Not applicable

3.6 Die Fabrication Reliability Test (Q100 Group D)

Test			Step	RESULTS	Notes
N	TEST NAME	CONDITIONS			
1	EM Electromigration	The data, test method, calculation and internal criteria should be available to the customer upon request for new technologies	Final result	DONE	Process qualification
2	TDDDB Time Dependent Dielectric Breakdown	The data, test method, calculation and internal criteria should be available to the customer upon request for new technologies	Final result	DONE	Process qualification
3	HCI Hot Carrier Injection	The data, test method, calculation and internal criteria should be available to the customer upon request for new technologies	Final result	DONE	Process qualification
4	NBTI Negative Bias Temperature Instability	The data, test method, calculation and internal criteria should be available to the customer upon request for new technologies	Final result	DONE	Process qualification
5	SM Stress Migration	The data, test method, calculation and internal criteria should be available to the customer upon request for new technologies	Final result	DONE	Process qualification

3.7 Electrical verification test (Q100 Group E)

Test			Step	RESULTS	Notes
N	TEST NAME	CONDITIONS			
1.a	ESD HBM	HBM = 2kV	Final result	PASSED	
1.b	ESD MM	MM = 200V	Final result	PASSED	
1.c	ESD CDM	CDM = 500V / 750V corner only	Final result	PASSED	
2.a	LU	Current Injection = Level B +/- 100 mA	Final result	PASSED	
2.b	LU	Supply Voltage = Level B 1.5xVmax	Final result	PASSED	
3	ED Electrical Distribution	[AEC Q100-009] <input checked="" type="checkbox"/> Testing at Room <input checked="" type="checkbox"/> Testing at Hot <input checked="" type="checkbox"/> Testing at Cold	Final result	DONE	
4	FG Fault Grading	[AEC Q100-007] FG shall be = or > 90% for qual units	Final result	DONE by Similarity	Pictus 512K Rousset
5	CHAR Characterization	[AEC Q103] Performed on new technologies and part families. <input type="checkbox"/> Testing at Room <input type="checkbox"/> Testing at Hot <input type="checkbox"/> Testing at Cold	Final result	N.P.	Not required by Q100

6	GL Electrothermally-Induced Gate Leakage	[AEC Q100-006] Test before and after GL at room temperature within 96hours of GL stress completion	Final result	DONE	
7	EMC Electromagnetic Compatibility	[SAE J1752/3 – radiated Emission]	Final result	N.P.	Not required by Q100
8	SC Short Circuit Characterization	[AEC Q100-012] Applicable to all smart power devices. This test and statistical evaluation shall be performed per agreement between user and supplier on a case-by-case basis.	Final result	N.A.	Not applicable to Microcontroller
9	SER Soft Error Rate	[JEDEC Un-accelerated: JESD89-1 or Accelerated: JESD89-2 & JESD89-3] Applicable to devices with memory sizes 1Mbit SRAM or DRAM based cells. Either test option (un-accelerated or accelerated) can be performed, in accordance to the referenced specifications. This test and its accept criteria is performed	Final result	DONE	

3.8 Defect Screening Test (Q100 Group F)

Test			Step	RESULTS	Notes
N	TEST NAME	CONDITIONS			
1	PAT Process Average testing	[AEC Q101]	Final result	IMPLEMENTED	
2	SBA Statistical Bin/Yield Analysis	[AEC Q102]	Final result	IMPLEMENTED	

4 REVISION TRACKING

Rev 1.1:

1. Added similarity for package trials in pag. 5,6
2. Added Package Assembly Integrity Test (Q100 Group C) table in page 9
3. Added die Fabrication Reliability Test (Q100 Group D) table in page 10
- 4.

Rev 1.0:

1. Package lot inserted in pag.4
2. Table of package trials added in pag.5,6
- 3: Cut 3.5 qualification strategy pag.3

Rev 0.6:

1. Format adjustment on header
2. Added Qualification ongoing statement (page 3)

Rev 0.5:

3. First document release with incomplete results available.

Rev 0.1: First document draft



SPC56 - M10 technology PCNs description

October 2013



SPC56 32 Bit - M10 90 nm

INDEX

2

LIST OF CHANGES

- Front End (wafer diffusion):
 - High volume manufacturing source activation: M10 process & product transfer from Rousset 8" to Crolles 12"
- EWS (electrical wafer sort):
 - Activation of second testing site in Rousset where not yet qualified
- Back End (assembly):
 - LQFP64/100 main source activation: package transfer from Muar to Malta
 - CuPd wire introduction



SPC56 32 Bit - M10 90 nm

Manufacturing Improvements

Device	Mem size	Package	C300	CuPd	Assy Muar to Malta	EWS Agr to R8	Design Fix
Pictus	256K	LQFP 64	X	X	X		
		LQFP 100	X	X	X		
		KGD + OPM					
	512K	LQFP 100	X	X	X		
		LQFP 144	X	X			
		LQFP 100	X	X	X		
1M	LQFP 144	X	X				
Bolero	256K	QFN					
		LQFP 64	X	X	X		
		LQFP 100	X	X	X		
	512K	QFN					X
		LQFP 64	X	X	X		X
		LQFP 100	X	X	X		X
		LQFP 144	X	X			X
	1.5M	LQFP 100	X	X	X	X	X
		LQFP 144	X	X		X	X
		LQFP 176	X	X		X	X
	3M	LQFP 176	X	X			X
		LQFP 208	X	X			X
BGA						X	

Device	Mem size	Package	C300	CuPd	Assy Muar to Malta	EWS Agr to R8	Design Fix
Leopard	1M	LQFP 100	X	X			
		LQFP 144	X	X			
		LQFP 100	X	X			
	2M	LQFP 144	X	X			
		BGA 257					
Monaco	1.5M	LQFP 144	X	X			X
		LQFP 176	X	X			X
Andorra	2M	BGA 324	X				X
		LQFP 176	X	X			X
	4M	BGA 324	X				X



SPC56 32 Bit - M10 90 nm

Manufacturing Improvements master plan

2012	2013												2014												2015				2016	2017
	J	F	M	A	M	J	J	A	S	O	N	D	J	F	M	A	M	J	J	A	S	O	N	D	Q1	Q2	Q3	Q4		



Bolero 1.5M EWS testing in Rousset

Pictus / Bolero LQFP 64 & 100 pin assembly in Kirkop

Andorra BGA assembly in Kirkop

Wafer diffusion

CuPd wire bonding

Bolero 1.5M EWS testing in Rousset

Pictus / Bolero LQFP 64 & 100 pin assembly in Kirkop

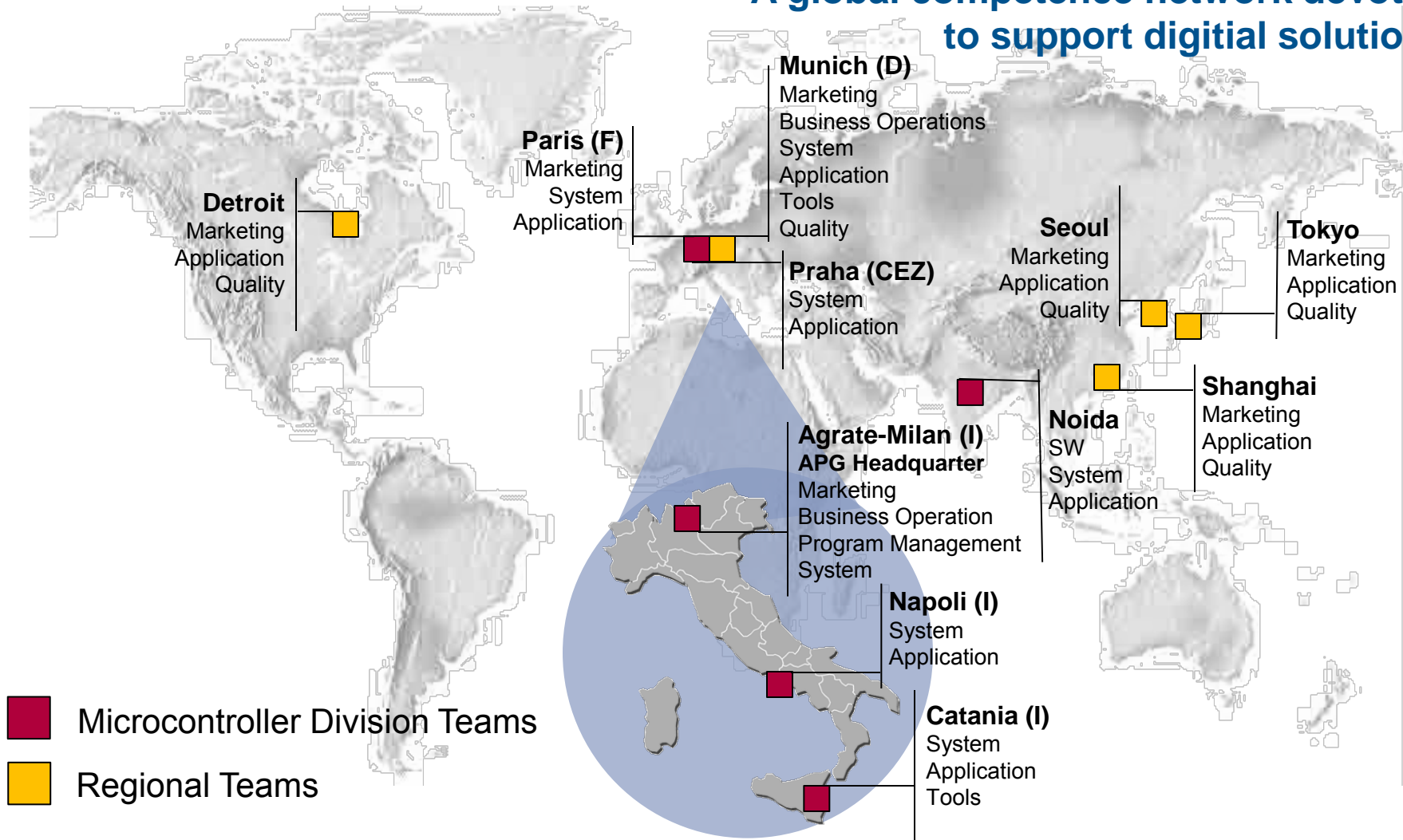
Andorra BGA assembly in Kirkop



APG – Microcontroller & ADAS Business Unit

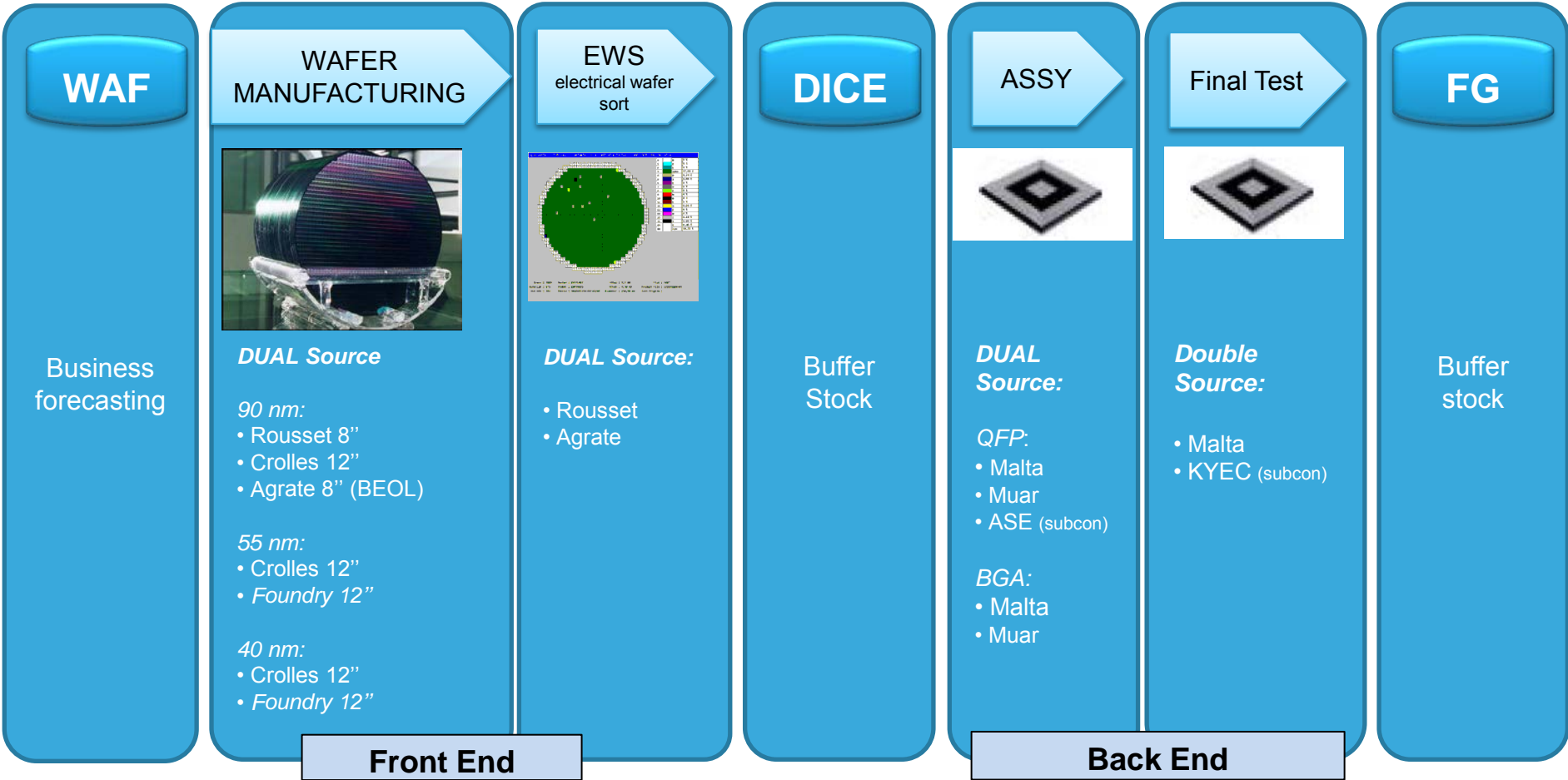
Main Locations Sites

A global competence network devoted to support digital solutions





SPC56 32 Bit - M10 90 nm Supply Chain structure

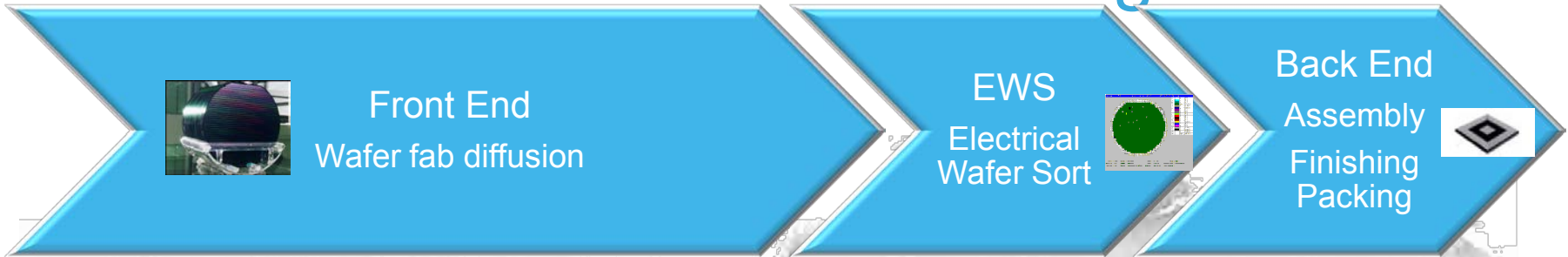


ST Manufacturing Strategy for advanced Automotive Microcontrollers is to use a main internal source and dual source capabilities (internal or subcon) to support large volumes, improve flexibility and secure business.



SPC56 32 Bit - M10 90 nm

ST Manufacturing sites - FE



Crolles (France) 8" & 12"

Rousset (France) 8"



Agrate (Italy) 8"

Catania (Italy) 6" & 8"



AMK (Singapore) 6" & 8"



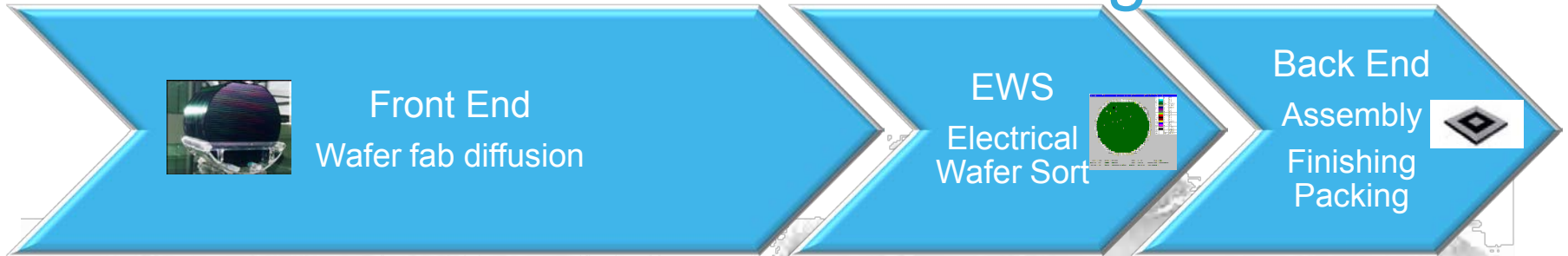
Microcontroller manufacturing sites

Although ST manufacturing facilities are worldwide diffused, microcontroller manufacturing is concentrated in Europe where the highest level of engineering competencies is kept by the Company



SPC56 32 Bit - M10 90 nm

ST Manufacturing sites - BE



Microcontroller manufacturing sites

Although ST manufacturing facilities are worldwide diffused, microcontroller manufacturing is concentrated in Europe where the highest level of engineering competencies is kept by the Company



SPC56 32 Bit - M10 90 nm Manufacturing strategy

- ST new process and product introduction strategy is to focus and stabilize industrialization and first months of production in an internal wafer fab
 - Rousset R8 8" for 90nm eNVM process (M10)
 - Crolles 300 12" for 55nm eNVM process (M55)
- A second wafer fab is enabled and qualified when production ramp up has been completed in the leading wafer fab and sufficient volumes are foreseen
- M10 90nm process used for the SPC56 family in Rousset R8 is now mature. To support the very high volumes expected over the next years Crolles 300 has been qualified
 - Crolles 300 (12" wafers): M10 technology qualified. Two products already qualified.
Product qualification end by Q1 2013



SPC56 32 Bit - M10 90 nm Manufacturing strategy

Technology	FAB A	FAB B	FAB C
BCD3	AMK6		
BCD4	AMK6	AG8	
BCD5	AMK6	AG8	
BCD6	AG8 + R2	CTN M5	
BCD8	CTN M5	AG8 + R2	
ViPM05	AMK6	CTN L1	CTN M5
ViPM07	CTN M5		
M10 (NVM 90nm)	R8	C300	R8 + R2
M55 (NVM 55nm)	C300	Foundry	
H11/H12	C300	Foundry	

Dual source strategy is applied inside ST on all technology families for automotive products thanks to in-house manufacturing capability



Secured Supply Chain

A true case study: ST managing Japan earthquake crisis

- ST vs our SUPPLIERS

- Crisis Management Team established at Corporate level
- Two main task forces: FE & BE
 - team members from Purchasing, Manufacturing, Quality, Planning
 - daily update to Corporate Management
- Communication to ST customers managed by PCN

- ***NO IMPACT ON ST DELIVERY***

- ST vs our CUSTOMERS

- ST directly involved by two major car makers to support with uC shipments as a back up for their Tier 2/3 impacted by Japan earthquake in Power Train and Safety related applications :

- 1st extraordinary delivery after 5 weeks from 1st contact
- 50% of customer run rate demand reached after 10 weeks
- **100% of customer run rate demand scheduled after 15 weeks**
- **NO CUSTOMER RETURN AFTER 3 YEAR AND 1M pcs SHIPPED IN THE FIRST YEAR**



90nm eNVM Production ramp-up Quality Performance

SPC56 ramp up in Automotive (K cumulate pcs)

60000

50000

40000

30000

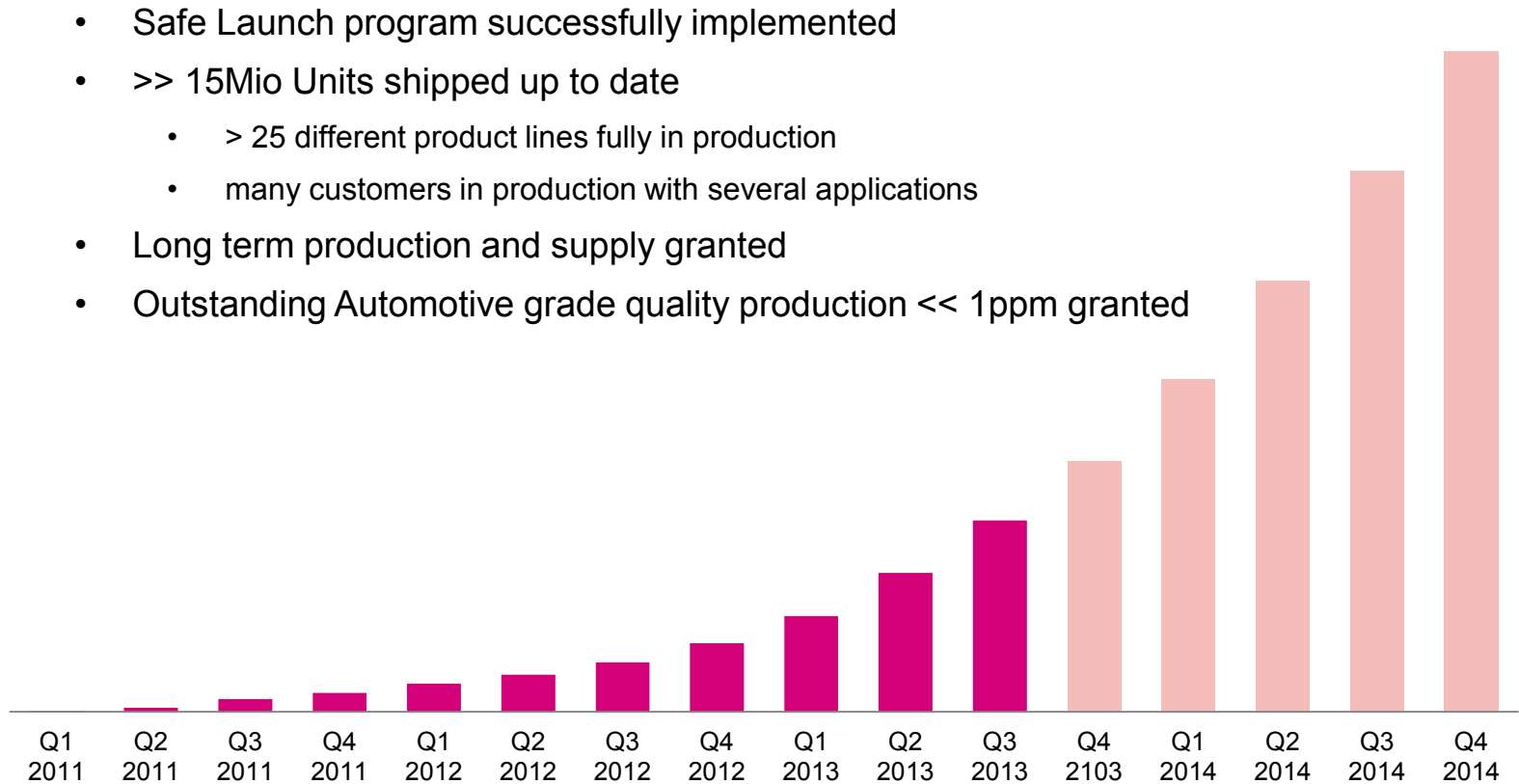
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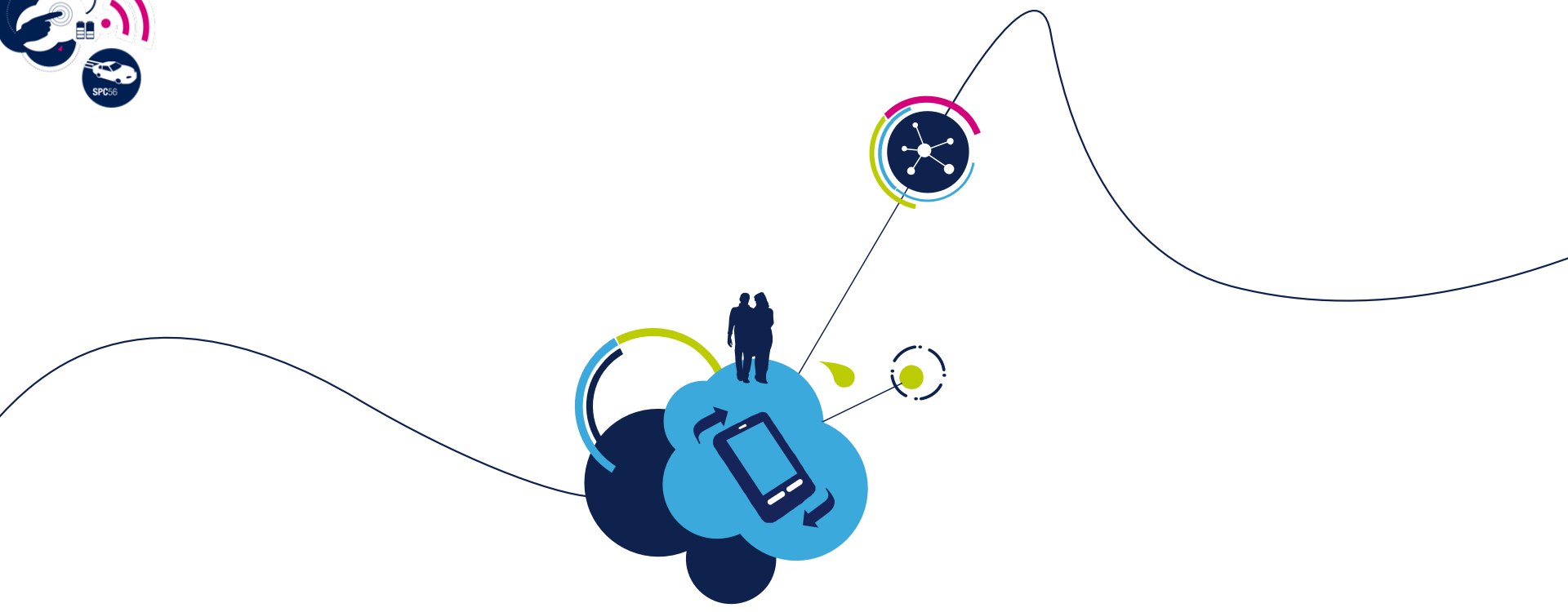
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Q1 2011 Q2 2011 Q3 2011 Q4 2011 Q1 2012 Q2 2012 Q3 2012 Q4 2012 Q1 2013 Q2 2013 Q3 2013 Q4 2013 Q1 2014 Q2 2014 Q3 2014 Q4 2014

- Safe Launch program successfully implemented
- >> 15Mio Units shipped up to date
 - > 25 different product lines fully in production
 - many customers in production with several applications
- Long term production and supply granted
- Outstanding Automotive grade quality production << 1ppm granted





M10 Front End Dual Sourcing

PCN APG-MID/13/7698



Crolles transfer global qualification strategy

- M10 TECHNOLOGY MAT30 done
- M10 TV (Pictus 512K, Andorra 4M) MAT30 done
- Similarity will be applied to qualify the M10 products, taking into account that Pictus 512K and Andorra 4M are already qualified:



CMOSM10 Crolles process: qualification plan

Product	Package	# lots Micro	similarity	# lots Flash	Similarity
Pictus 256K	LQFP100 LQFP64	1	Pictus 512K	1	Pictus 512K
Pictus 512K	LQFP144 LQFP100	3	No	3	No
Pictus 1M	LQFP100 LQFP144	1	Pictus 512K	1	Pictus 512K
Bolero 256K	LQFP100 LQFP64	1	Pictus 512K	1	Pictus 512K
Bolero 512K	LQFP144 LQFP100 LQFP64	1	Pictus 512K	1	Pictus 512K
Bolero 1.5M	LQFP176	1	Pictus 512K	1	Pictus 512K
Bolero 3M	LQFP176	1	Pictus 512K	1	Pictus 512K
Monaco 1.5M	LQFP100 LQFP144 LQFP176	3	No	3	No
Andorra 2M	LQFP176	1	Andorra 4M Leopard 1M	1	Andorra 4M Leopard 1M Leopard 2M
Andorra 4M	LQFP176	3	No	3	No
Leopard 1M	LQFP100 LQFP144	1	Andorra 4M Andorra 2M	1	Andorra 2M Andorra 4M Leopard 2M
Leopard 2M	LQFP100 LQFP144	1	Andorra 4M Andorra 2M	1	Andorra 2M Andorra 4M Leopard 1M



SPC56 32-Bit M10 90 nm FE Manufacturing Dual Source strategy

2012	2013												2014												2015				2016	2017
	J	F	M	A	M	J	J	A	S	O	N	D	J	F	M	A	M	J	J	A	S	O	N	D	Q1	Q2	Q3	Q4		



▲
1 MU shipped
▲
15 MU shipped

Rousset R8 8'': current production site for 4 & 6 metal SPC56 (M10 – 90nm) products

M10 90nm 4&6 Metals volume production



Crolles C300 12'': high capacity production site for 4 & 6 metal SPC56 (M10 – 90nm) products

M10 90nm high volume production

M10 90nm 6 Metals ramp up

M10 90nm 4 Metals ramp up



Agrate R2 8'': additional site for back end of line (contact / metal / vias) steps on Rousset wafers

M10 90nm Rousset FEOL + Agrate BEOL 4 Metal products



SPC56 32 Bit - M10 90 nm

Internal FE Manufacturing sites

Rousset	Current	Potential
8" /200mm Capacity	7500 wafers/week	6000 wafers/week full Cu
Product Start	CY2000	
Clean room	7300m ²	9500m ²
Investissement to date	\$1.8 B	
Technologies in production	0.35µm to 90nm	65/55nm
Class	Mini environnement concept (class 1)	
Employees	2722 (total site, including EWS, Divisions and Support Functions)	
Crolles 300	Current	Potential
12" /300mm Capacity	3500 wafers/week	4500 wafers/week
Product Start	CY2003	
Clean room	10000m ²	
Investissement to date	\$1.55 B	
Technologies in production	90nm down to 40nm	32nm down to 22nm
Class	Mini environnement concept (class 1)	
Employees	>5000 (total site, including contractors, partners, and R&D)	



SPC56 32 Bit - M10 90 nm

Rousset plant





SPC56 32 Bit - M10 90 nm

Crolles 300 mm





Embedded non-volatile memory

Technology & Manufacturing Challenges

- Change in eFlash technology development & manufacturing environment
 - Very few companies in the world able to develop & manufacture eFlash
 - Stand-alone NVM manufacturers more and more separated from eFlash manufacturers
 - Very few Auto eFlash MCU supplier keep in-house production capabilities



“Nano2017” R&D Program Announced at STMicroelectronics’ Crolles Site

Five-year strategic R&D program led by ST to further advance the company’s leadership in key embedded processing solutions and technologies

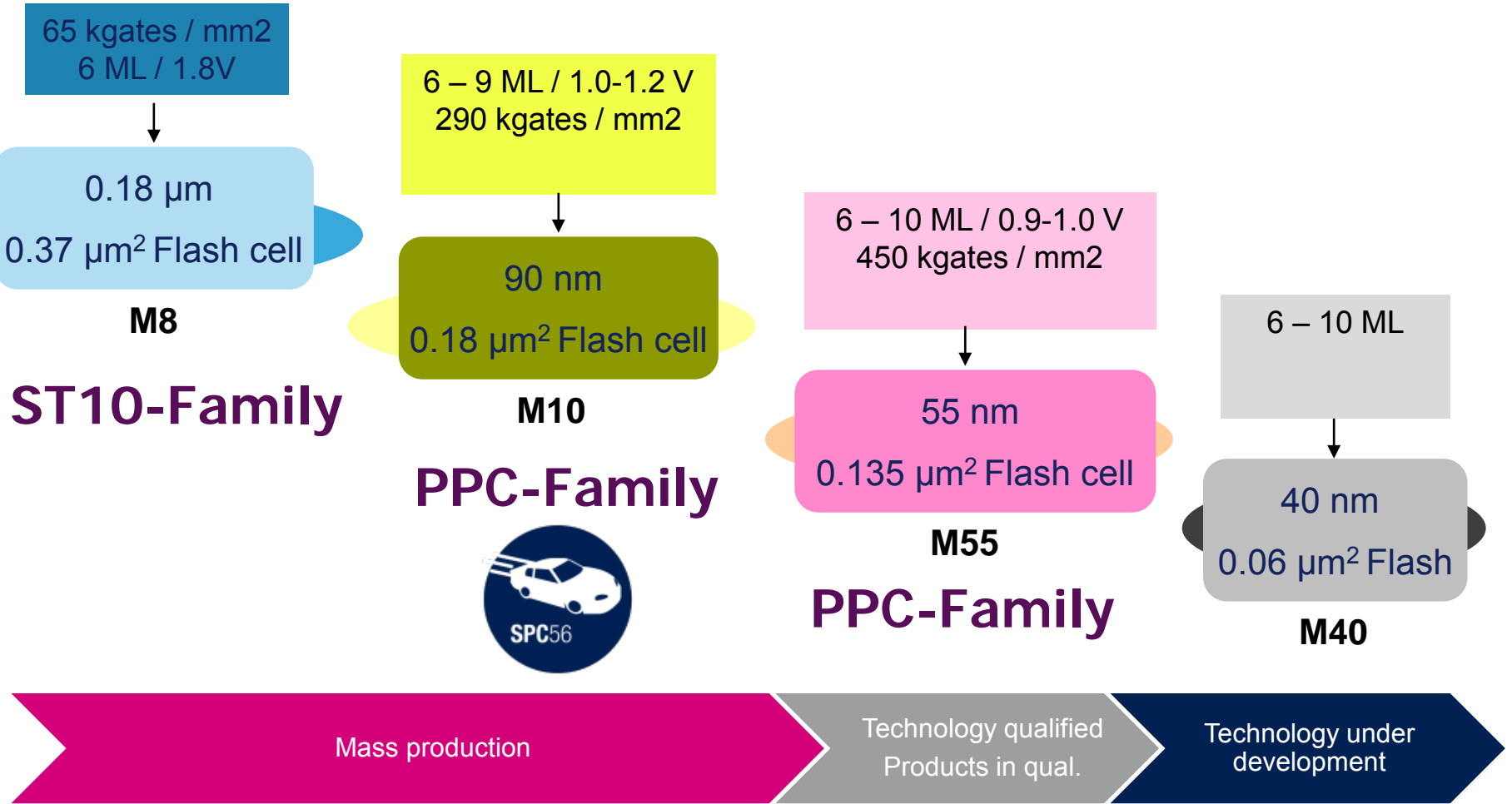


ST recently announced a dedicated investment plan for Crolles 12” (C300) wafer fab



SPC56 32 Bit - M10 90 nm

Leadership in embedded flash technology



ST has been a major player in the stand alone flash memory market prior to integrate them inside MCU device
ST is a global player in embedded MCU since 25 years over three different technology node: M6Y, M8, M10



SPC56 32 Bit - M10 90 nm Crolles300 : Facilities

• Clean room

- surface
- air conditioning
- vibration

10 000 m² class ISO4 @ 0.1 μm + 2000 m² B2 building
Foup + mini-environnement class ISO2 @0.1 μm
6.500.000 m³ / h
21.5°C +/- 0.5 °C temperature
45% +/- 2 % hygrometry
3 μm / s (V+H) RMS

• Fluids

- Ultra-pure water
- Gases
- Chemicals

18.2 Mohm.cm
1 ppb pour le TOC
20 ppt pour les chlorures
100 ppt (O2: 1 ppb)
1-10 ppb

• Power supply

- average
- UPS

25 MW
17 MW

300 mm
FOUP

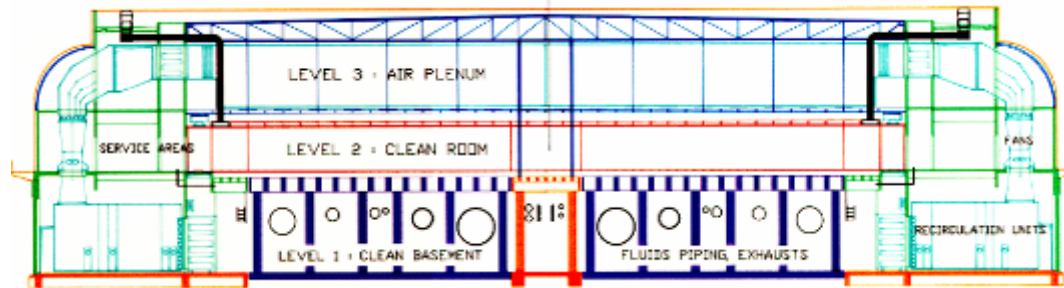


~ 9 kg with
25 wafers

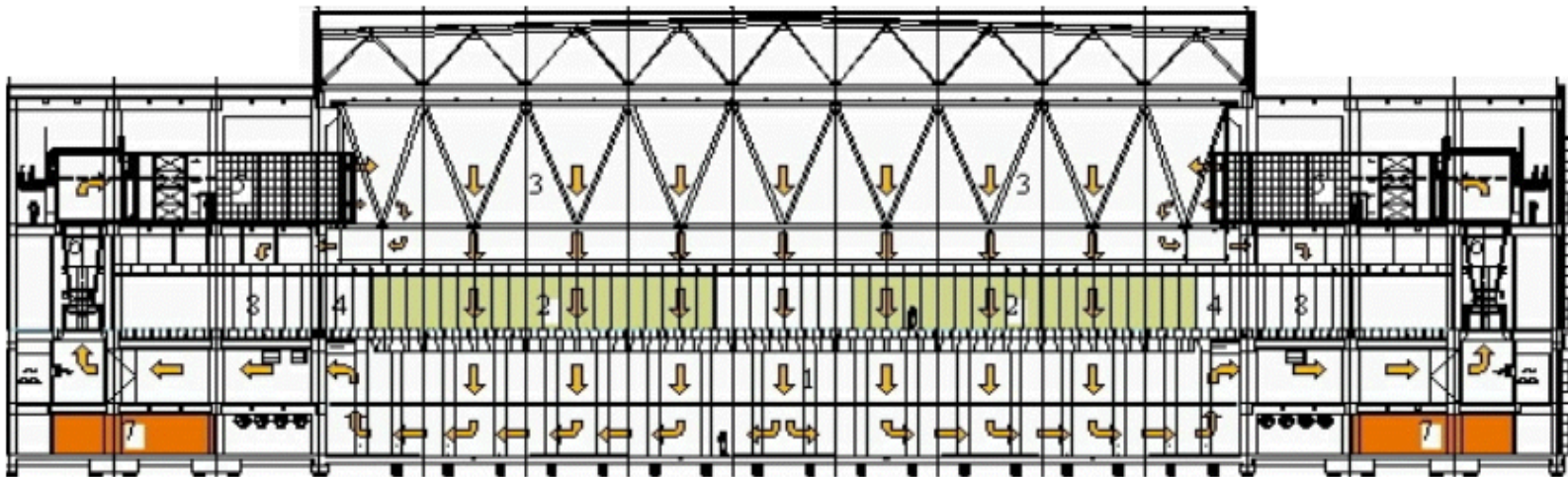


SPC56 32 Bit - M10 90 nm

Crolles 300 mm vs. Crolles 200 mm



Crolles200 : from 0.35 μm to 0.12 μm
Crolles300 : from 90 nm to 22 nm



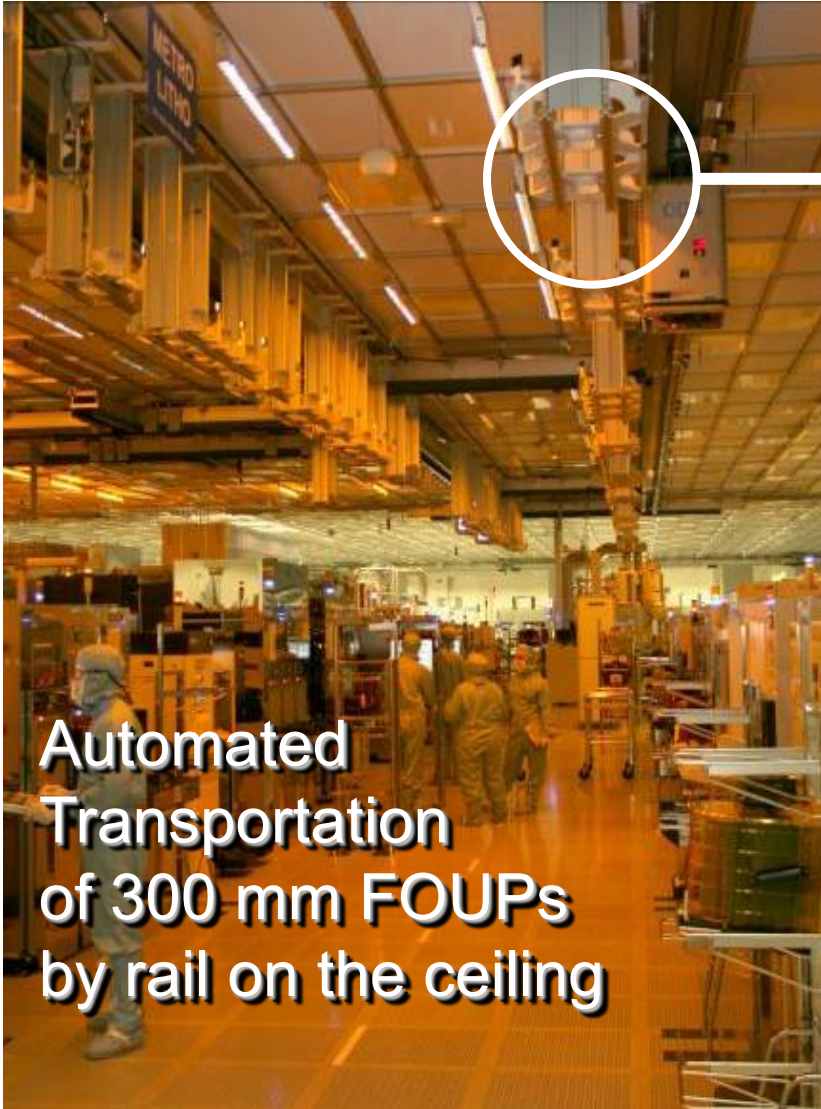


SPC56 32 Bit - M10 90 nm Clean Room 300 mm





SPC56 32 Bit - M10 90 nm Clean Room 300 mm





SPC56 32 Bit - M10 90 nm Crolles300 Facilities Overview



Process exhausts
580 000 m³/h



Power:

Installed = 39 MVA

Peak demand = 15.6 MVA

Fab demand = 7.5 MVA

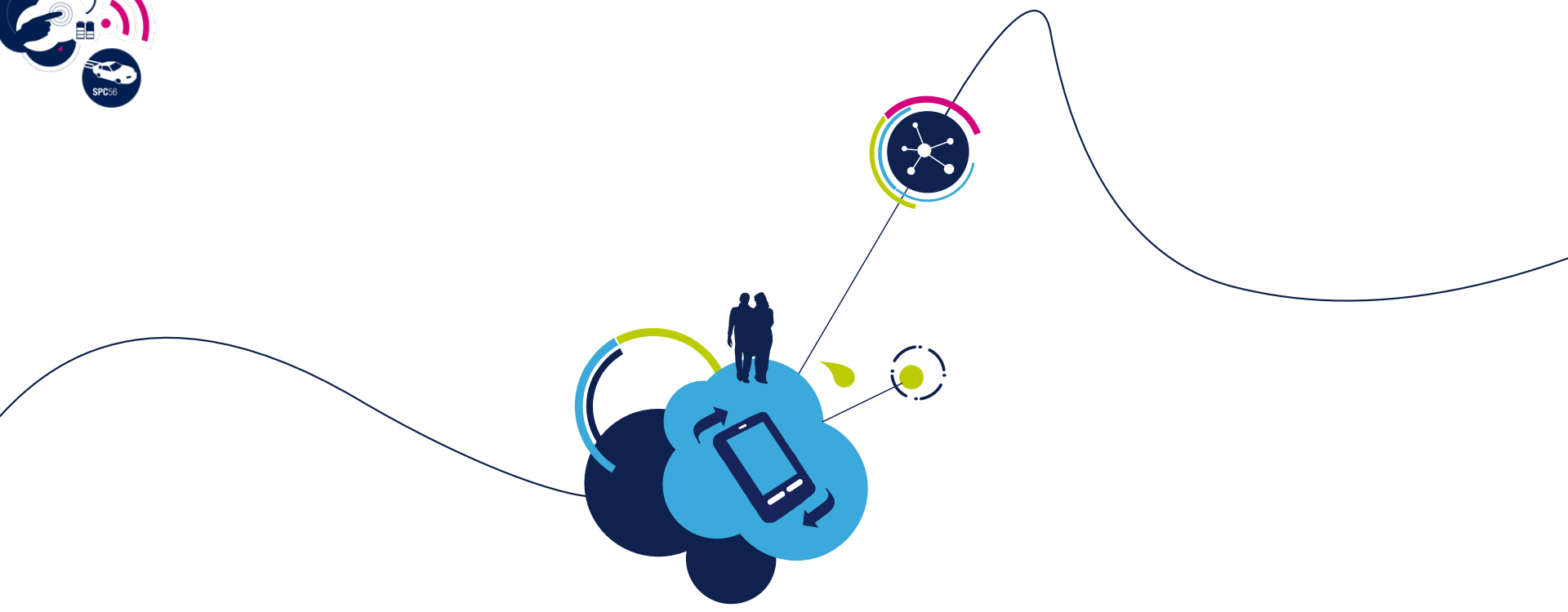
Facilities = 8.1 MVA



80 m³/h Ultra Pure Water Plant



30 MW cooling capacity



M10 Back End Dual Sourcing

PCN APG-MID/13/7972



SPC56 32-Bit M10 90 nm BE Manufacturing Dual Source strategy

2012	2013												2014												2015				2016	2017
	J	F	M	A	M	J	J	A	S	O	N	D	J	F	M	A	M	J	J	A	S	O	N	D	Q1	Q2	Q3	Q4		



LQFP 100 (14x14) ULA / 144 (20x20) / 176 (24x24) volume production

Kirkkop: current production site for high pin count QFP & BGA *BGA 15x15 / 17x17 / 23x23*

LQFP 64 (10x10) / 100 (14x14) volume production



Muar

BGA 15x15 / 17x17 / 23x23

LQFP 64 (10x10) / 100 (14x14)

Muar

LQFP 208 (28x28)



SPC56 32 Bit - M10 90 nm

LQFP64 / 100 dual Source Back End

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- ST has successfully executed the first step of its manufacturing strategy for assembly with the industrialization and ramp-up of SCP56 family in Malta (QFP high pin count: 100, 144, 176 pins) and Muar (QFP low pin count: 64, 100 pin)
- With the projected growth of SPC56 production volumes and to secure Customer deliveries in case emergency situations, ST is now aggressively qualifying and ramping-up production of:

LQFP64 (10x10) & 100 (14x14) in Malta

- Process has been qualified
- ST will introduce CuPd wires on some of its packages



SPC56 32 Bit - M10 90 nm

Similarity for Product Family

LQFP100 (14x14)

- Package already qualified and in production on FL60 (Leopard 1M)
- FL60 Package reliability report is included in PCN.
- Similarity criteria (defined by an ST specification: ADCS 7028386) for package qualification have been verified and met.
- FL60, FP40, FP50, FP60, FB50 and FB64 microcontrollers belong to the same product family.
- LQFP-100 14x14 Package qualification in Malta using FL60 is extended to FP40, FP50, FP60, and FB50 and FB64 microcontrollers.



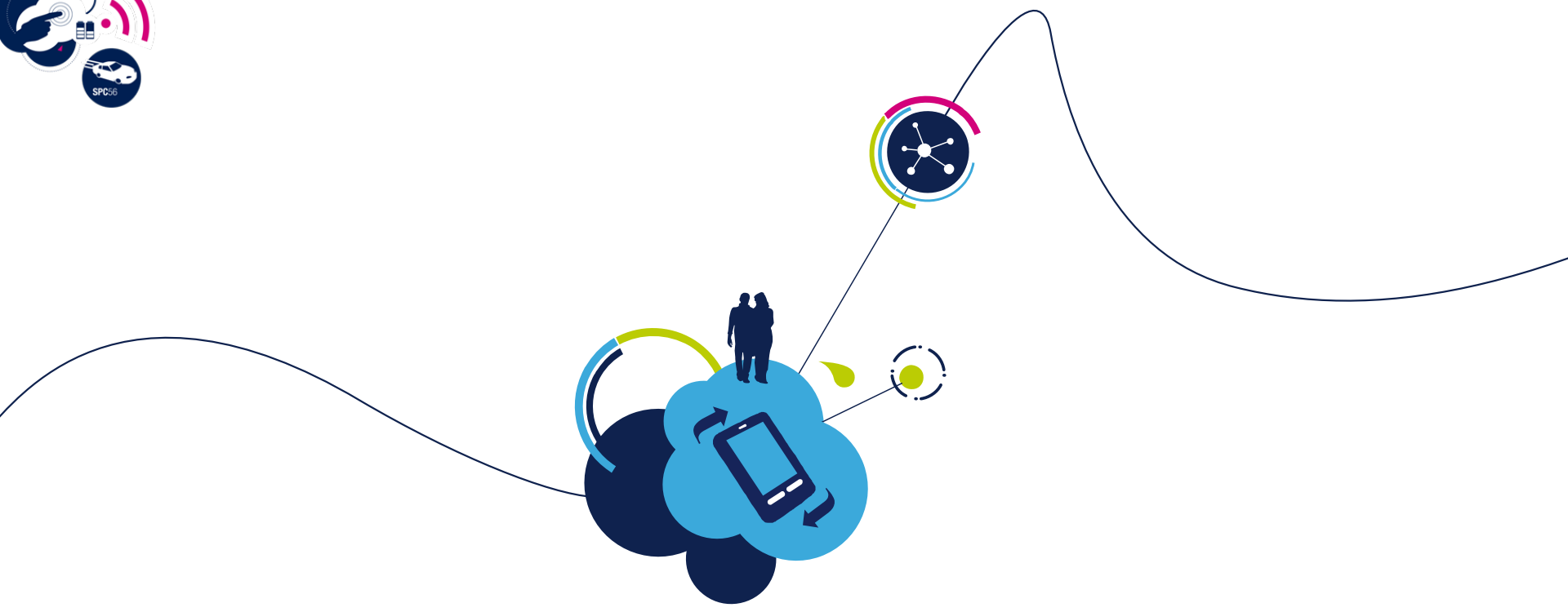
SPC56 32 Bit - M10 90 nm

LQFP64 / 100 dual Source Back End

LQFP64 (10x10)

- Dedicated qualification exercise based on available similarities

Trial	Conditions	Samples x Assy Lot
HTOL	1k cyc @ 125°C + 168hrs HTOL@125°C (1000hrs monitor)	77 x 1
ELFR	BI + 24hrs	800 x 1
TC	1000cyc -50°C/+150°C	77 x 3
AC	96h	77 x 3
THB	1000h 85°C/85%	77 x 3
HTS	1000hrs@150°C	77 x 1
CA	---	on 3 assy lots



Copper wire qualification



SPC56 32 Bit - M10 90 nm

Cu wire qualification

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- CuPd wire will be used in M10 products
- Qualification exercise has to be run both on 4 metal and 6 metal option
- Similarities can be used evaluating bonding parameters and bill of material between:
 - 4 metal products (Pictus, Bolero)
 - 6 metal products (Andorra, Monaco, Leopard, Bolero 3M)



SPC56 32 Bit - M10 90 nm CuPd qualification status

- 6 metal process option

- Mat 10 (feasibility assessment) done
- Mat 20: three assembly lots with bonding corner conditions running
- Mat 30 for 6M1T process option running

Similarity between LQFP176 and LQFP144 packages:

- Same complexity from process point of view, both are 6M1T
- Same pad class and same Bond Pad Opening = 52um
- Same assembly line
- Line stressing planned on 30K parts to assess manufacturability

- 4 metal process option

- Mat 10 done
- Mat 20: three assembly lots with bonding corner conditions running
- Mat 30: three assembly lots in standard bonding condition running
 - Line stressing planned on 30K parts to assess manufacturability

- Samples

- On customer request starting from

Q4 2013



4 Metal M10 Products in LQFP: QUAL PLAN for CuPd introduction

Products	LQFP Packages	Qualifications	Comments
Pictus512k	LQFP100	PACKAGE VALIDATION + Q100	Full qualification
	LQFP144	Q100	By similarities with Monaco 1.5M LQFP144 and Andorra 4M LQFP176
Pictus256k	LQFP64	PACKAGE VALIDATION + Q100	Full qualification
	LQFP100	NO TRIALS REQUIRED	Similarities with Pictus 512K LQFP100
Pictus1M	LQFP100	1 LOT OF TC REQUIRED BECAUSE BIGGER DIE SIZE	Similarities with Pictus 512K LQFP100
	LQFP144	1 LOT OF TC REQUIRED BECAUSE BIGGER DIE SIZE	Similarities with Pictus 512K LQFP144
Bolero256k	LQFP64	NO TRIALS REQUIRED	Similarities with Pictus 256K LQFP64
	LQFP100	NO TRIALS REQUIRED	Similarities with Pictus 512K LQFP100
Bolero512k	LQFP64	1 LOT OF TC REQUIRED BECAUSE BIGGER DIE SIZE	Similarities with Pictus 256K LQFP64
	LQFP100	NO TRIALS REQUIRED	Similarities with Pictus 512K LQFP100
	LQFP144	NO TRIAL REQUIRED	Similarities with Pictus 512K LQFP144
Bolero1M5	LQFP100	1 LOT OF TC REQUIRED BECAUSE BIGGER DIE SIZE	Similarities with Pictus 512K LQFP100
	LQFP144	1 LOT OF TC REQUIRED BECAUSE BIGGER DIE SIZE	Similarities with Pictus 512K LQFP144
	LQFP176	1 LOT OF TC REQUIRED BECAUSE BIGGER DIE SIZE	By similarities with Andorra 4M LQFP176 and Pictus 512K LQFP144



6 Metal M10 Products in LQFP: QUAL PLAN for CuPd introduction

Products	Packages	Qualifications	Comments
Andorra 4M	LQFP176	PACKAGE VALIDATION + Q100	Shared with Monaco1M5 LQFP144
Monaco 1M5	LQFP144	PACKAGE VALIDATION + Q100	Shared with Andorra 4M LQFP176
	LQFP100	PACKAGE VALIDATION + Q100	Package similarities with LQFP100 4 metal option qualification
	LQFP176	NO TRIALS REQUIRED	By similarities with Monaco 1.5M LQFP144 and Andorra 4M LQFP176
Andorra 2M	LQFP176	NO TRIALS REQUIRED	By similarities with Monaco 1.5M LQFP144 and Andorra 4M LQFP176
Leopard 1M	LQFP100	NO TRIALS REQUIRED	Similarity with Leopard 2M
	LQFP144	NO TRIALS REQUIRED	Similarity with Leopard 2M
Leopard 2M	LQFP100	PACKAGE VALIDATION + Q100	Package similarities with LQFP100 4 metal option qualification
	LQFP144	PACKAGE VALIDATION + ONLY 1 LOT OF TC REQUIRED BECAUSE BIGGER DIE SIZE	Similarities with Pictus 512K and Monaco 1.5M LQFP144
Bolero 3M	LQFP176	NO TRIALS REQUIRED	Similarities with Pictus 512K, Leopard 1M and Andorra 4M

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